

L Number	Hits	Search Text	DB	Time stamp
1	44271	sic or (silicon adj carbide)	USPAT;	2002/11/12 08:13
			US-PGPUB	
2	6785	(sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:13
		mosfet)	US-PGPUB	
3	373	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:32
		mosfet)) and (anneal\$4 same ("h.sub.2" or hydrogen))	US-PGPUB	
4	225	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 07:59
		mosfet)) and (anneal\$4 near12 ("h.sub.2" or hydrogen))	US-PGPUB	
5	41	(sic or (silicon adj carbide)) same (anneal\$4 near12	USPAT;	2002/11/12 08:13
1		("h.sub.2" or hydrogen))	US-PGPUB	
6	25	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 07:55
		mosfet)) and ((sic or (silicon adj carbide)) same (anneal\$4	US-PGPUB	
_		near12 ("h.sub.2" or hydrogen)))	LIGDAT	00004440 00:44
7	1163	(nitrid\$8 or "n.sub.2 o" or "no" or (nitrous adj oxide) or (nitric	USPAT;	2002/11/12 08:11
		adj oxide) or nitrogenation) same (anneal\$4 near12	US-PGPUB	
`	66	("h.sub.2" or hydrogen)) ((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:01
8	66	mosfet)) and ((nitrid\$8 or "n.sub.2 o" or "no" or (nitrous adj	US-PGPUB	2002/11/12 00.01
		oxide) or (nitric adj oxide) or nitrogenation) same (anneal\$4	03-FGF06	
		near12 ("h.sub.2" or hydrogen)))		
10	0	((oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or	USPAT;	2002/11/12 08:11
10		hydrogen))) and ((sic or (silicon adj carbide)) same	US-PGPUB	2002/11/12/00/11
		(semiconductor or mos or mosfet))	00, 0, 02	
11	1	((oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or	USPAT:	2002/11/12 08:11
	, i	hydrogen))) and (sic or (silicon adj carbide))	US-PGPUB	
9	43	(oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or hydrogen))	USPAT;	2002/11/12 08:12
			US-PGPUB	
12	56448	sic or (silicon adj carbide)	EPO; JPO;	2002/11/12 08:13
			DERWENT;	
	•		IBM_TDB	
13	5373	(sic or (silicon adj carbide)) same (semiconductor or mos or	EPO; JPO;	2002/11/12 08:36
		mosfet)	DERWENT;	
			IBM_TDB	
14	12	((sic or (silicon adj carbide)) same (semiconductor or mos or	EPO; JPO;	2002/11/12 08:13
		mosfet)) and (anneal\$4 near12 ("h.sub.2" or hydrogen))	DERWENT;	
45		//sis su /silisam adi saubida)\ agus s /sausisam dusAsm as us sa	IBM_TDB	2002/11/12 00:24
15	20	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT; US-PGPUB	2002/11/12 08:34
16	24	mosfet)) same (anneal\$4 same ("h.sub.2" or hydrogen)) ((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:35
16	24	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) same ("n.sub.2 o")	US-PGPUB	2002/11/12 00:33
17	2	((sic or (silicon adj carbide)) same (semiconductor or mos or	EPO; JPO;	2002/11/12 08:37
''		mosfet)) same ("n.sub.2 o" or n2o)	DERWENT;	2002/11/12 00:07
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